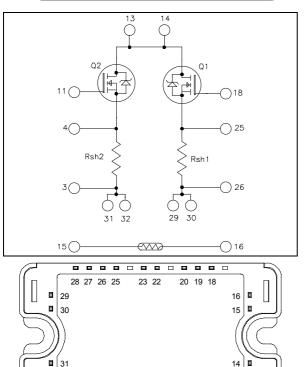


Linear MOSFET **Power Module** 



#### Pins 13/14 ; 29/30 ; 31/32 must be shorted together

7 8

## Absolute maximum ratings (per leg)

۵

32

2 3 4

| Symbol            | Parameter   |                     | Max ratings | Unit |
|-------------------|---|---------------------|-------------|------|
| V <sub>DSS</sub>  | Drain - Source Breakdown Voltage                  |                     | 200         | V    |
| т                 | Continuous Drain Current $T_c = 23$               |                     | 109*        |      |
| I <sub>D</sub>    | Continuous Drain Current                          | $T_c = 80^{\circ}C$ | 81*         | А    |
| I <sub>DM</sub>   | Pulsed Drain current                              |                     | 400         |      |
| V <sub>GS</sub>   | Gate - Source Voltage                             |                     | $\pm 30$    | V    |
| R <sub>DSon</sub> | Drain - Source ON Resistance                      |                     | 19          | mΩ   |
| PD                | Maximum Power Dissipation $T_c = 25^{\circ}C$     |                     | 480         | W    |
| I <sub>AR</sub>   | Avalanche current (repetitive and non repetitive) |                     | 100         | А    |
| E <sub>AR</sub>   | Repetitive Avalanche Energy                       |                     | 50          | mI   |
| E <sub>AS</sub>   | Single Pulse Avalanche Energy                     |                     | 3000        | 1113 |
| E <sub>AR</sub>   | Repetitive Avalanche Energy                       |                     | 50          | m    |

14

13

10 11 12

\* Output current per leg must be limited to 44A ( $a_{c}$  T<sub>C</sub>=25°C and 31A ( $a_{c}$  T<sub>C</sub>=80°C to not exceed the shunt specification. • In saturation mode

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

# APTML202UM18R010T3AG

# $V_{DSS} = 200V$ $R_{DSon} = 18m\Omega \text{ typ} @ Tj = 25^{\circ}C$ $I_D = 109A^*$ (a) $Tc = 25^{\circ}C$

#### Application

• Electronic load dedicated to power supplies and battery discharge testing

#### Features

- Linear MOSFET
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance •

#### **Benefits**

- Direct mounting to heatsink (isolated package)
- easy series and parallels combinations for power and voltage improvements
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- **RoHS** Compliant

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# All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

# Electrical Characteristics (per leg)

| Symbol              | Characteristic                  | Test Conditions                         |         | Min | Тур | Max  | Unit |  |
|---------------------|---------------------------------|---|---------|-----|-----|------|------|--|
| I <sub>DSS</sub>    | Zero Gate Voltage Drain Current | $V_{DS} = 200V$ ; $V_{GS} = 0V$ $T_j =$ | = 25°C  |     |     | 25   |      |  |
|                     |                                 | $V_{DS} = 160V$ ; $V_{GS} = 0V$ $T_j =$ | = 125°C |     |     | 250  | μA   |  |
| R <sub>DS(on)</sub> | Drain – Source on Resistance    | $V_{GS} = 10V, I_D = 50A$               |         |     | 18  | 19   | mΩ   |  |
| V <sub>GS(th)</sub> | Gate Threshold Voltage          | $V_{GS} = V_{DS}, I_D = 2.5 \text{mA}$  |         | 2   |     | 4    | V    |  |
| I <sub>GSS</sub>    | Gate – Source Leakage Current   | $V_{GS} = \pm 30 \text{ V}$             |         |     |     | ±100 | nA   |  |

#### Dynamic Characteristics (per leg)

| Symbol           | Characteristic               | Test Conditions     | Min | Тур  | Max | Unit |
|------------------|------------------------------|---------------------|-----|------|-----|------|
| C <sub>iss</sub> | Input Capacitance            | $V_{GS} = 0V$       |     | 9880 |     |      |
| C <sub>oss</sub> | Output Capacitance           | $V_{\rm DS} = 25 V$ |     | 2320 |     | pF   |
| C <sub>rss</sub> | Reverse Transfer Capacitance | f = 1 MHz           |     | 700  |     |      |

#### Shunt Electrical Characteristics (per leg)

| Symbol          | Characteristic   |                      | Min | Тур | Max | Unit |
|-----------------|------------------|----------------------|-----|-----|-----|------|
| R <sub>sh</sub> | Resistance value |                      |     | 10  |     | mΩ   |
| T <sub>sh</sub> | Tolerance        |                      |     | 2   |     | %    |
| D               |                  | T <sub>C</sub> =25°C |     |     | 20  | W    |
| $P_{sh}$        |                  | T <sub>C</sub> =80°C |     |     | 10  | vv   |
| I <sub>sh</sub> | Current capacity | T <sub>c</sub> =25°C |     |     | 44  | ٨    |
|                 |                  | T <sub>C</sub> =80°C |     |     | 31  | A    |

# **Temperature sensor PTC**

Downloaded from: http://www.datasheetcatalog.com/

| Symbol           | Characteristic          |                   | Min   | Тур   | Max   | Unit  |
|------------------|-------------------------|-------------------|-------|-------|-------|-------|
| R <sub>25</sub>  | Resistance @ 25°C       |                   | 1980  |       | 2020  | Ω     |
| $R_{100}/R_{25}$ | Resistance ratio        | Tamb=100°C & 25°C | 1.676 | 1.696 | 1.716 |       |
| $R_{-55}/R_{25}$ | Resistance ratio        | Tamb=-55°C & 25°C | 0.48  | 0.49  | 0.50  |       |
| В                | Temperature coefficient |                   |       | 7900  |       | ppm/K |

#### Thermal and package characteristics

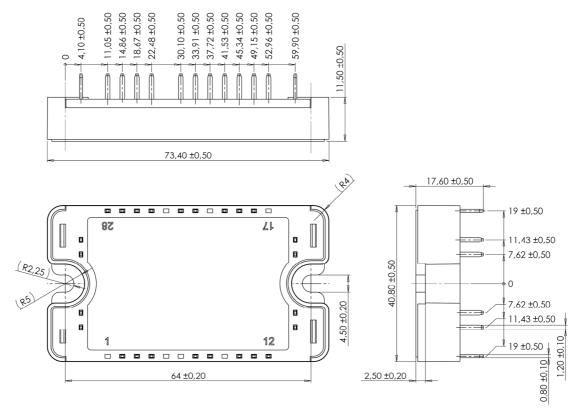
| Symbol            | Characteristic  |            |          | Min  | Тур | Max  | Unit |
|-------------------|---|------------|----------|------|-----|------|------|
| R <sub>thJC</sub> | Junction to Case Thermal Resistance                           | MOSFET (   | per leg) |      |     | 0.26 | °C/W |
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz |            |          | 4000 |     |      | V    |
| T <sub>J</sub>    | Operating junction temperature range                          |            |          | -40  |     | 150  |      |
| T <sub>STG</sub>  | Storage Temperature Range                                     |            |          | -40  |     | 125  | °C   |
| T <sub>C</sub>    | Operating Case Temperature                                    |            |          | -40  |     | 100  |      |
| Torque            | Mounting torque 7   | o heatsink | M4       | 2    |     | 3    | N.m  |
| Wt                | Package Weight  |            |          |      |     | 110  | g    |

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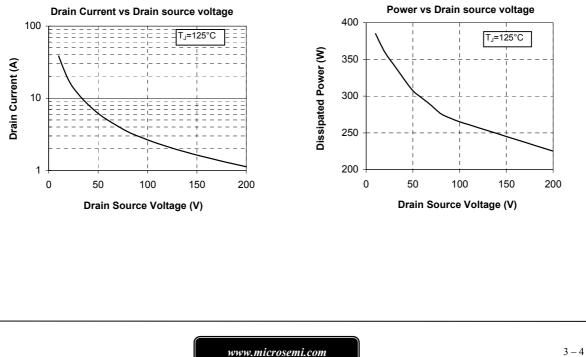


#### SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

## **Typical Performance Curve (linear mode) (per leg)**



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